

Vishay Siliconix

P-Channel 1.8 V (G-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)		
	0.290 at V _{GS} = - 4.5 V	± 0.91		
- 12	0.435 at V _{GS} = - 2.5 V	± 0.74		
	0.580 at V _{GS} = - 1.8 V	± 0.64		

FEATURES

- Halogen-free According to IEC 61249-2-21
 Definition
- TrenchFET[®] Power MOSFETs: 1.8 V Rated
- Compliant to RoHS Directive 2002/95/EC



Available

SOT-323 SC-70 (3-LEADS) G 1 S 2 Top View



Ordering Information: Si1307DL-T1-E3 (Lead (Pb)-free) Si1307DL-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, ur	nless otherwi	se noted		
Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 12		v
Gate-Source Voltage		V _{GS}	± 8		
	T _A = 25 °C	- I _D	± 0.91	± 0.85	-
Continuous Drain Current $(T_J = 150 \text{ °C})^a$	T _A = 70 °C		± 0.72	± 0.68	
Pulsed Drain Current		I _{DM}	± 3		A
Continuous Diode Current (Diode Conduction) ^a		۱ _S	- 0.28	- 0.24	l
Maximum Davies Disain ational	T _A = 25 °C	- P _D	0.34	0.29	w
Maximum Power Dissipation ^a	T _A = 70 °C		0.22	0.19	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 5 s	- R _{thJA} R _{thJF}	315	375	°C/W
Maximum Junction-to-Amblent	Steady State		360	430	
Maximum Junction-to-Foot (Drain)	Steady State		285	340	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -250 \ \mu A$	- 0.45			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, \text{ V}_{GS} = \pm 8 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -9.6 V, V_{GS} = 0 V$			- 1	μA	
		$V_{DS} = -9.6 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 ^{\circ}\text{C}$			- 5		
On-State Drain Current ^a	I _{D(on)}	V _{DS} - 5 V, V _{GS} = - 4.5 V	- 3			А	
	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 1 A		0.240	0.290		
Drain-Source On-State Resistance ^a		V _{GS} = - 2.5 V, I _D = - 0.5 A		0.350	0.435	Ω	
		V _{GS} = - 1.8 V, I _D = - 0.3 A		0.480	0.580		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 5 V, I _D = - 1 A		3.5		S	
Diode Forward Voltage ^a	V _{SD}	I _S = - 1 A, V _{GS} = 0 V			- 1.2	V	
Dynamic ^b							
Total Gate Charge	Qg			3.2	5	nC	
Gate-Source Charge	Q _{gs}	V_{DS} = - 6 V, V_{GS} = - 4.5 V, I_{D} = - 1 A		0.59			
Gate-Drain Charge	Q _{gd}			0.56			
Turn-On Delay Time	t _{d(on)}			7.5	12		
Rise Time	t _r	V_{DD} = - 6 V, R_L = 4 Ω		32	45	ns	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 1 Å, V_{GEN} = - 4.5 V, R_g = 6 Ω		17	25		
Fall Time	t _f			11.5	20		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1 A, dl/dt = 100 A/μs		32	52		

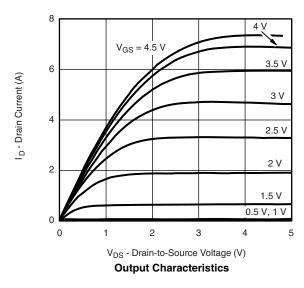
Notes:

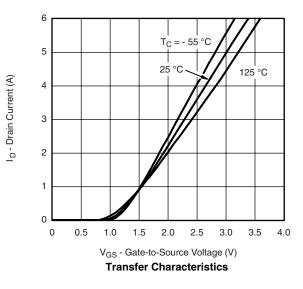
a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

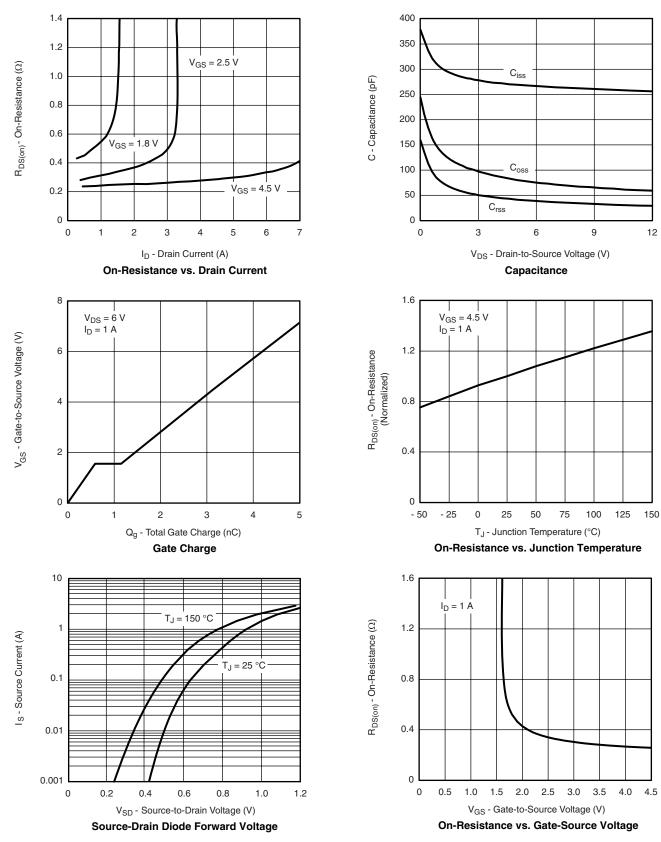






Si1307DL Vishay Siliconix

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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Si1307DL

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted 0.4 20 0.3 16 $I_D = 250 \ \mu A$ 0.2 12 V_{GS(th)} (V) Power (W) 0.1 T_A = 25 °C 8 0.0 4 - 0.1 - 0.2 0 - 50 - 25 0 25 50 75 100 125 150 10⁻³ 10⁻² 10-1 600 10 100 1 T_{.1} - Temperature (°C) Time (s) **Single Pulse Power Threshold Voltage** 2 1 Duty Cycle = 0.5 Normalized Effective Transient Thermal Impedance ТП 0.2 П Notes -0.1 P_{DM} 0.1 0.05 t₁ t2 t₁ 0.02 1. Duty Cycle, D = 2. Per Unit Base = R_{thJA} = 360 °C/W 3. T_{JM} - $T_A = P_{DM}Z_{thJA}^{(t)}$ Single Pulse 4. Surface Mounted 0.01 10-4 10⁻³ 10-2 10-1 10 100 600 1 Square Wave Pulse Duration (s) Normalized Thermal Transient Impedance, Junction-to-Ambient 2 1 Normalized Effective Transient Thermal Impedance Duty Cycle = 0.5 0.2 0.1 0.1 0.05 0.02 Single Pulse 0.01 10-4 10⁻³ 10⁻² 10-1 1 10 Square Wave Pulse Duration (s) Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <u>www.vishay.com/ppg271077</u>.





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